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P-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY V_{DS} (V) $R_{DS(on)}$ (mΩ)(Typ.) I_D (A)^a Q_g (Typ.) - 150 140 at V_{GS} = - 10 V - 30 35 nC

FEATURES

- DT-Trench Power MOSFET
- 100 % R_q and UIS Tested
- Excellent package for good heat dissipation

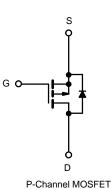
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APPLICATIONS

- · Load switch
- · Industrial applications







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ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 150	V	
Gate-Source Voltage	V _{GS}	± 20	v		
Continuous Drain Current (T _J = 150° C) ^a	T _C = 25 °C		- 30	А	
	T _C = 100 °C	─ I _D	- 22		
Pulsed Drain Current ^b		I _{DM}	- 120		
Single Avalanche Energy		E _{AS}	150	mJ	
Maximum Power Dissipation ^c	T _C = 25 °C	D	110	W	
	T _C = 100 °C	$ P_D$	44	VV	
Operating Junction and Storage Temperature R	Range	T _J , T _{stg}	- 55 to + 150	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.13	C/VV	

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{BJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA		-	-	.,
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 2	-	- 4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	-	-	± 100	nA
Zana Cata Valtana Dunia Cuma d		V _{DS} = -150 V, V _{GS} = 0 V	V _{DS} = -150 V, V _{GS} = 0 V		- 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -120V, V _{GS} = 0 V, T _J = 55 °C	-	-	- 10	μA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥– 5 V, V _{GS} = - 10 V	- 30	-	-	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 10 A	-	140	200	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 10 A	-	15	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	4000	-	pF
Output Capacitance	Coss	V _{GS} = 0 V, V _{DS} = - 75 V, f = 1 MHz	-	71	-	
Reverse Transfer Capacitance	C _{rss}		-	65	-	
Total Gate Charge ^c	Q_g		-	35	-	nC
Gate-Source Charge ^c	Q _{gs}	V _{DS} = -75 V, V _{GS} = -10 V, I _D = -10 A	-	4.5	-	
Gate-Drain Charge ^c	Q_{gd}		-	6.8	-	
Gate Resistance	R _g	f = 1 MHz	-	3.5	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	17.5	-	
Rise Time ^c	t _r	$V_{DD} = -75 \text{ V}, R_{q} = 3 \Omega,$	-	11	-	
Turn-Off Delay Time ^c	t _{d(off)}	I _D = - 10 A , V _G s = - 10 V	-	68	-	ns
Fall Time ^c	t _f		-	29	-	
Drain-Source Body Diode Ratings and	Characterist	tics ^b (T _C = 25 °C)				
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	- 30	А
Pulsed Current	I _{SM}		-	-	- 120	Α
Forward Voltage ^a	V_{SD}	I _F = - 1 A, V _{GS} = 0 V	-	-	-1.2	٧
Reverse Recovery Time	t _{rr}	I _F = - 10 A, di/dt = 100 A/μs	-	55	-	ns
Reverse Recovery Charge	Q_{rr}	i _F = - 10 A, αι/αι – 100 Α/μς	-	200	-	nC

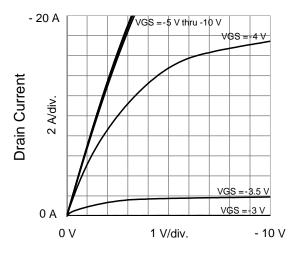
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

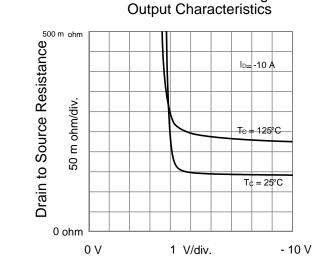
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



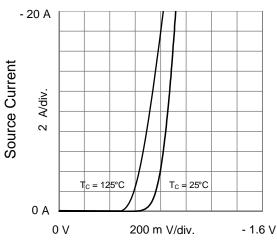
TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



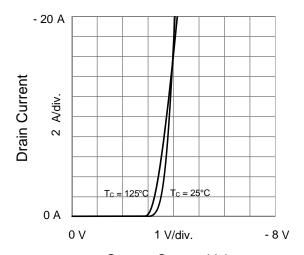
Drain to Source Voltage Output Characteristics



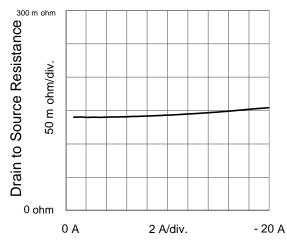
Gate to Source Voltage Drain to Source Resistance vs. Gate to Source Voltag



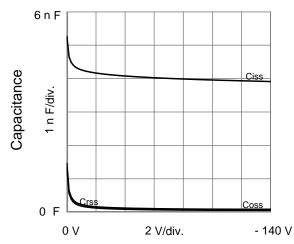
Source to Drain Voltage **Body Diode Forward Characteristics**



Gate to Source Voltage Transfer Characteristics



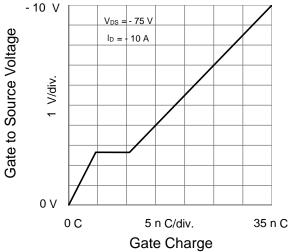
Drain Current



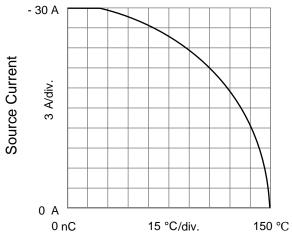
Drain to Source Voltage Capacitances



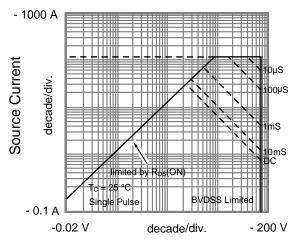
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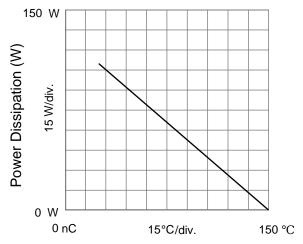
Gate to Source Voltage vs. GateCharge



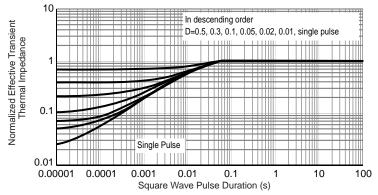
T_C - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Case



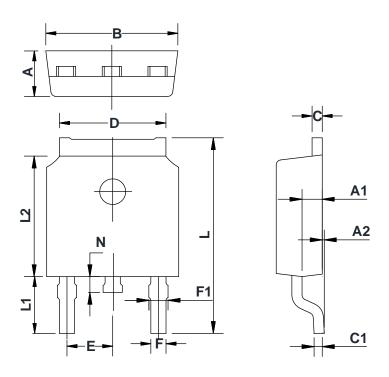
T_C - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEA SURE=MILLIMETER)

Symbol	Min	Тур	Max
А	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
В	6.40	6.60	6.80
С	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
Е	2.286 TYP		
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
Г	9.30	9.90	10.80
L1	2.40	2.80	3.60
L2	5.90	6.10	6.55
N	0.57	0.80	1.05





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